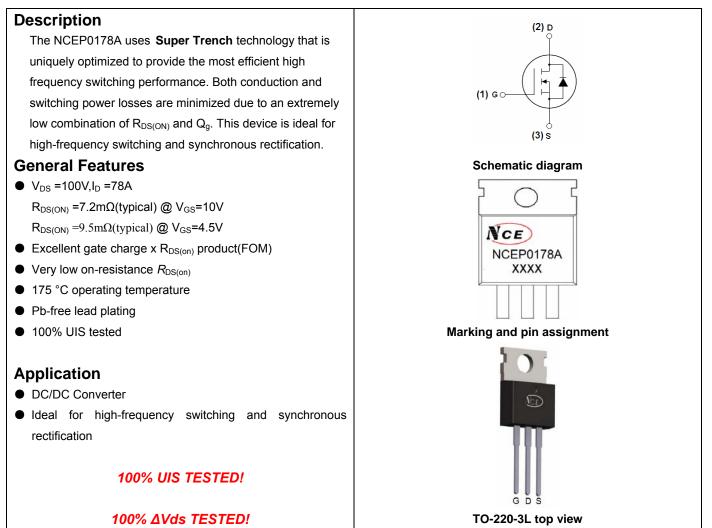




# NCE N-Channel Super Trench Power MOSFET



## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP0178A	NCEP0178A	TO-220-3L	-	-	-

## Absolute Maximum Ratings (T<sub>c</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	100	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I <sub>D</sub>	78	A
Drain Current-Continuous(T <sub>C</sub> =100 ℃)	I <sub>D</sub> (100℃)	60	Α
Pulsed Drain Current	I <sub>DM</sub>	320	A
Maximum Power Dissipation	PD	125	W
Derating factor		0.83	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	320	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C





**NCEP0178A** 

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	1.2	°C <b>/W</b>
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## Electrical Characteristics (T<sub>C</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.2	1.7	2.2	V
Durain Course On Chata Desintance	P	V <sub>GS</sub> =10V, I <sub>D</sub> =39A	-	7.2	8.5	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =39A	-	9.5	12	mΩ
Forward Transconductance	<b>G</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =39A	40	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>		-	4200	5480	PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =50V, $V_{GS}$ =0V,	-	354	425	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	23	30	PF
Switching Characteristics (Note 4)			•			L
Turn-on Delay Time	t <sub>d(on)</sub>		-	15	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =50V,I <sub>D</sub> =39A	-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V,R <sub>G</sub> =4.7 $\Omega$	-	41	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	6	-	nS
Total Gate Charge	Qg	N/ 50)// 00A	-	65		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =50V,I <sub>D</sub> =39A,	-	15.3		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	9		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =78A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	78	А
Reverse Recovery Time	t <sub>rr</sub>	$T_J$ = 25°C, $I_F$ = $I_S$	-	101		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	193		nC
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(10003)}$	-	193		

#### Notes:

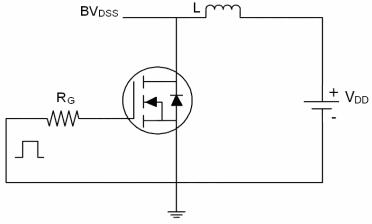
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t  $\leq$  10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^\circ \!\! C$  ,V\_{DD}=50V ,V\_G=10V ,L=0.5mH ,Rg=25  $\!\Omega$



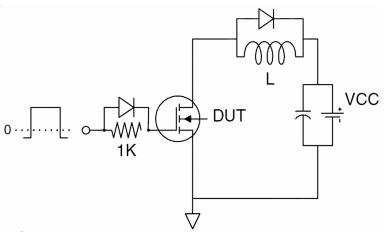
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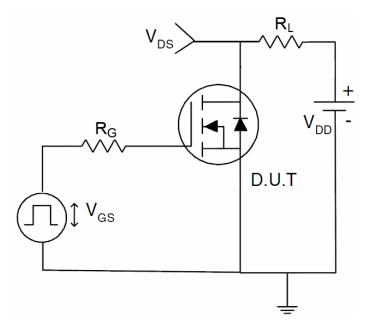
## Test Circuit 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit



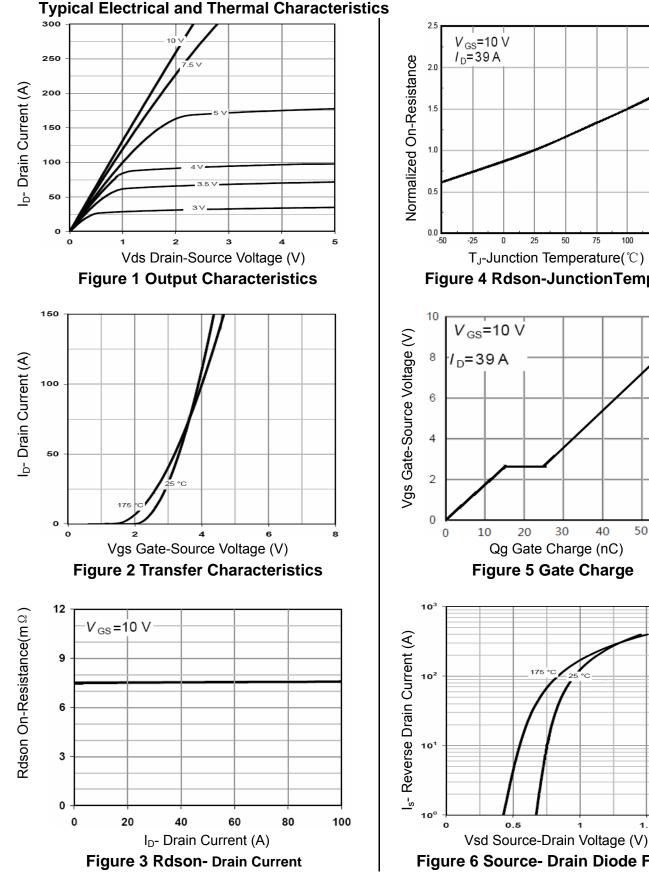
3) Switch Time Test Circuit

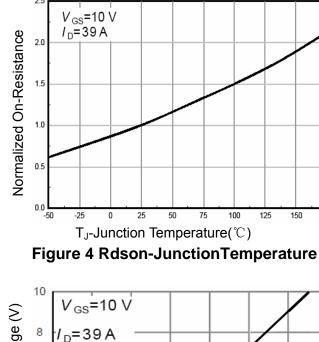




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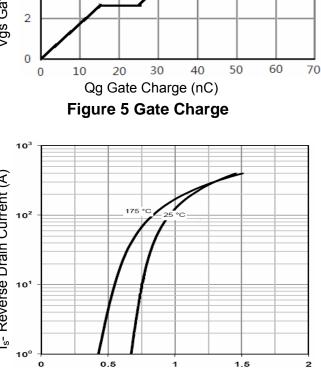


Figure 6 Source- Drain Diode Forward



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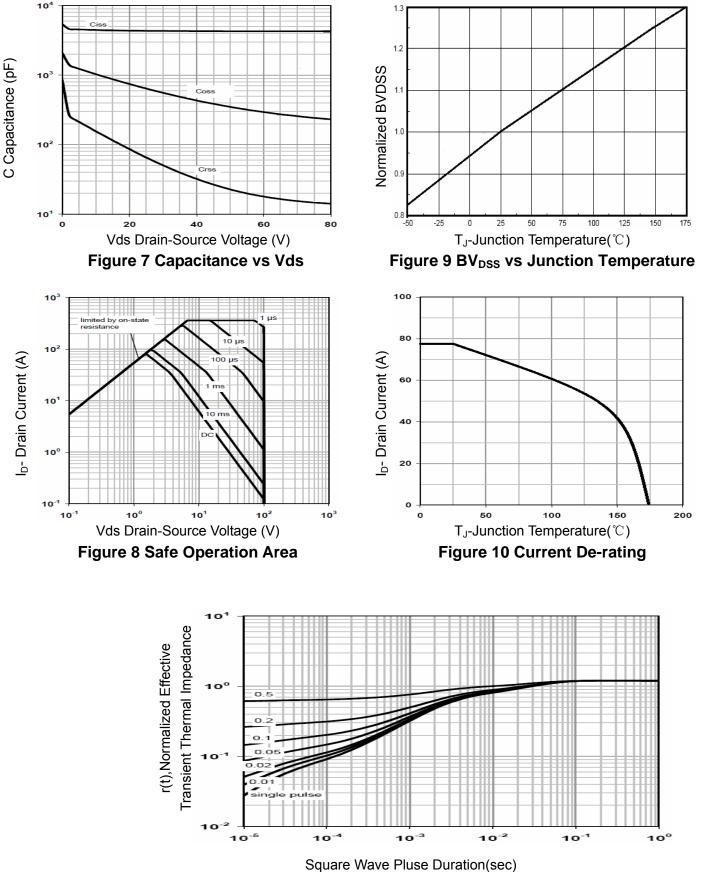


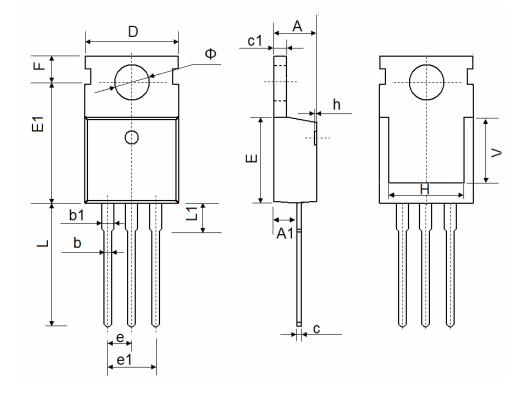
Figure 11 Normalized Maximum Transient Thermal Impedance



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## **TO-220-3L Package Information**



Symphol	Dimensions	s In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.54	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295	REF.	
Ф	3.400	3.800	0.134	0.150	





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